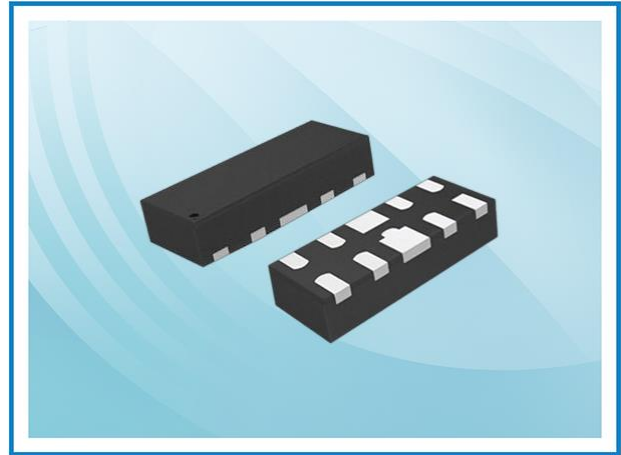


PTUC0524PA-H – ESD Protection Diode

Feature

- 30 Watts peak pulse power (8/20μs)
- Unidirectional configurations
- Solid state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (C_j = 0.2pF typ. I/O to I/O)
- IEC61000-4-2 (ESD) ±15kV (Air), ±12kV (Contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)
- IEC61000-4-5 (Lightning): 3A (8/20μs)



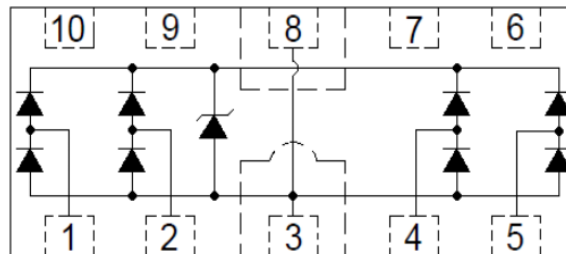
Applications

- USB3.0, USB2.0, Ethernet
- HDMI 2.0, Displayport 1.3, eSATA
- Unified Display Interface
- Digital Video Interface
- High Speed Serial Interface

Mechanical Data

- Tiny DFN10L(2.5mmx1.0mm) package
- Molding compound flammability rating: UL94V-0
- Tape and Reel Packaging
- RoHS/WEEE Compliant

Schematic and PIN Configuration



Maximum Rating

Parameter	Symbol	Value	Unit
IEC61000-4-2 ESD Voltage – Air Mode	V _{ESD} ⁽¹⁾	±15	kV
IEC61000-4-2 ESD Voltage – Contact Mode		±12	
Peak Pulse Power (t _p =8/20μs)	P _{PP}	30	W
Peak Pulse Current (t _p =8/20μs) (note1)	I _{PP}	3	A
Lead Solder Temperature (10 seconds duration)	T _L	260	°C
Junction Temperature	T _J	-55~125	°C
Storage Temperature Range	T _{stg}	-55~125	°C

Note:

1. Device stressed with ten non-repetitive ESD pulses.
2. Non-repetitive current pulse 8/20μs exponential decay waveform according to IEC61000-4-5.
3. All ratings are measured at environmental temperature of TA = 25 °C unless otherwise noted.

PTUC0524PA-H – ESD Protection Diode

Electrical Characteristics

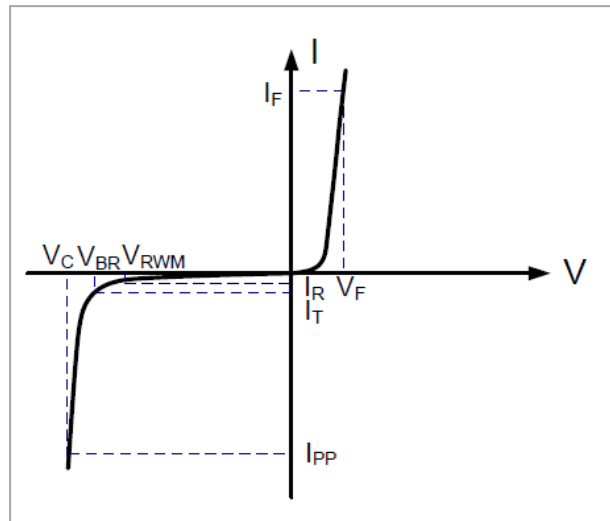
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Stand-off Voltage	$V_{RWM}^{(1)}$				5.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	6.0	7.2	9.5	V
Reverse Leakage Current	I_R	$V_{RWM} = 5.0$			0.5	μA
Clamping Voltage	$V_C^{(2)}$	$I_{PP} = 3\text{A}$		10	14	V
Junction Capacitance	C_J	$V_R = 0\text{V}, f = 1\text{MHz}, I/O \text{ to } I/O$		0.20	0.3	pF
		$V_R = 0\text{V}, f = 1\text{MHz}, I/O \text{ to } \text{GND}$		0.36	0.5	pF

Note:

1. Other voltages available upon request.
2. Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC61000-4-5.
3. All ratings are measured at environmental temperature of $T_A = 25^\circ\text{C}$ unless otherwise noted.

Electrical Parameters

Symbol	Parameter
V_C	Clamping Voltage @ I_{PP}
I_{PP}	Peak Pulse Current
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_R	Reverse Leakage Current @ V_{RWM}
V_{RWM}	Reverse Stand-off Voltage
V_F	Forward Voltage @ I_F



PTUC0524PA-H – ESD Protection Diode

Typical Characteristics

Fig.1 Peak Pulse Power Rating Curve

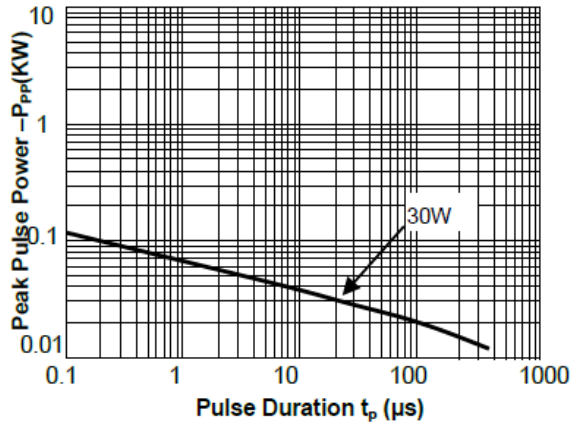


Fig.2 Pulse Derating Curve

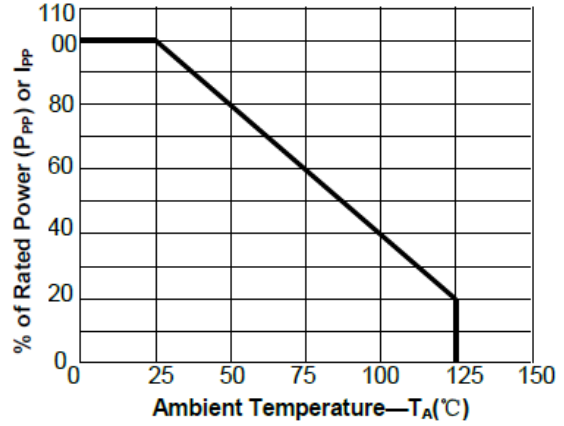


Fig.3 Pulse Waveform-8/20 μs

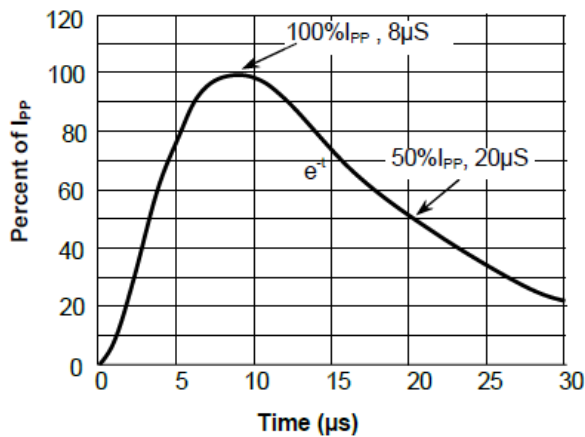


Fig.4 Pulse Waveform-ESD(IEC61000-4-2)

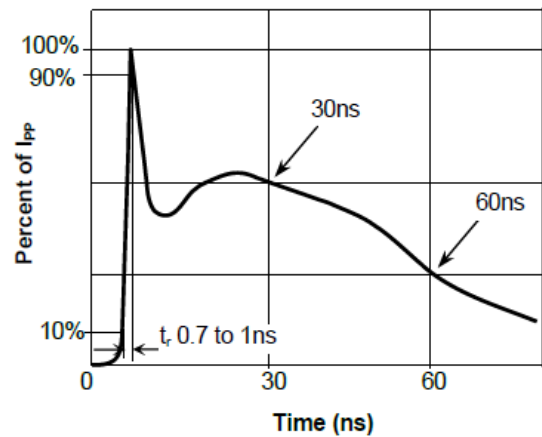


Figure5: Positive Clamping voltage (TLP)

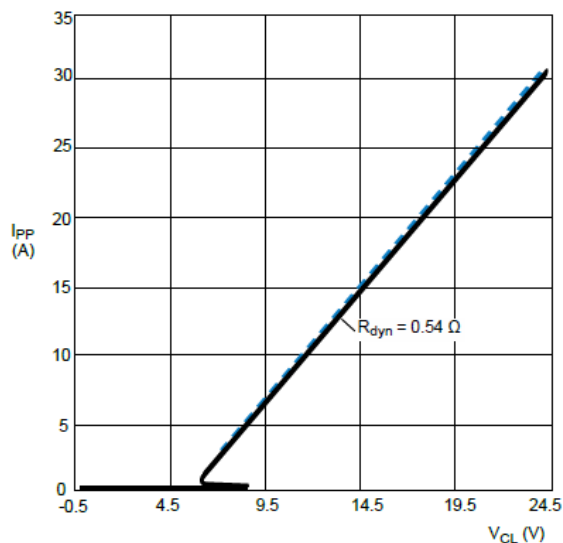
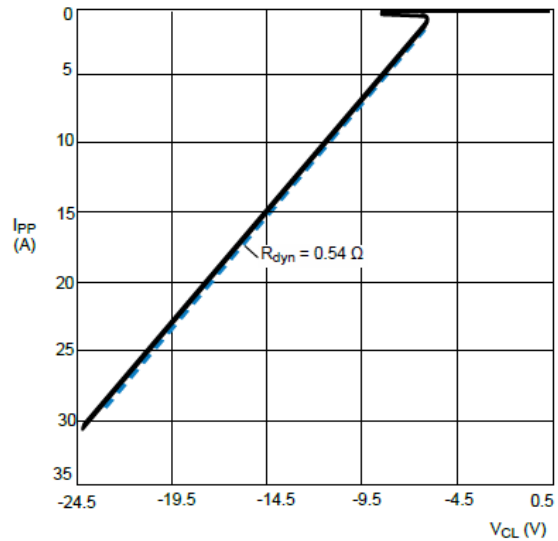
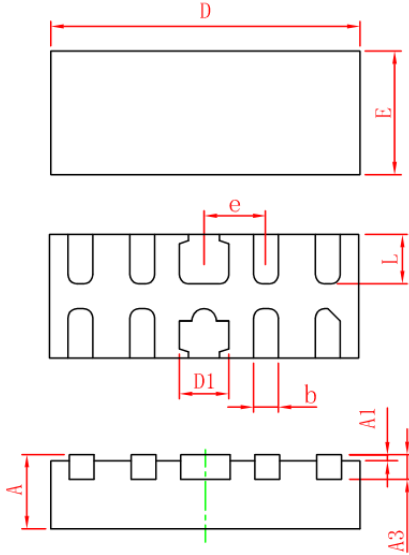


Figure6: Negative Clamping voltage (TLP)



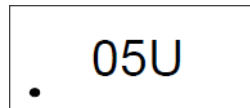
PTUC0524PA-H – ESD Protection Diode

DFN10L(2.5mmx1.0mm) Package Outline Dimensions



Symbol	Dimensions (mm)		
	Min	Nom	Max
A	0.45	0.50	0.60
A1	-	0.02	0.05
A3	0.10	0.15	0.20
D	2.45	2.50	2.55
E	0.95	1.00	1.05
D1	0.35	0.40	0.45
b	0.15	0.20	0.25
e	0.50BSC		
L	0.35	0.40	0.45

Marking



Packaging Information

Order Code	Packaging	Reel Size	PCS/Reel
PTUC0524PA-H	DFN10L(2.5x1.0mm)	7 inch	3,000